



# UPS140e3

## 1.0 A Schottky Barrier Rectifier

### DESCRIPTION

The Microsemi UPS140e3 Powermite<sup>®</sup> Schottky rectifier is RoHS compliant and offers optimized forward voltage characteristics with reverse blocking capabilities up to 40 Volt. They are ideal for surface mount applications that operate at high frequencies.

In addition to its size advantages, Powermite<sup>®</sup> package features include a full metallic bottom that eliminates possibility of solder flux entrapment during assembly, and a unique locking tab acts as an efficient heat path from die to mounting plane for external heat sinking with very low thermal resistance junction to case (bottom). Its innovative design makes this device ideal for use with automatic insertion equipment.

### KEY FEATURES

- Low thermal resistance DO-216 package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

**IMPORTANT:** For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

### ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Rectified Output Current (at rated $V_R$ , $T_C=135^\circ\text{C}$ )	$I_o$	1.0	A
Peak Repetitive Forward Current (at rated $V_R$ , square wave, 100kHz, $T_C=135^\circ\text{C}$ )	$I_{FRM}$	2.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave	$I_{FSM}$	50	A
Voltage Rate of Change (rated $V_R$ , $T_J=25^\circ\text{C}$ )	dv/dt	10,000	V/ $\mu\text{s}$
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Junction Temperature	$T_J$	-55 to +125	$^\circ\text{C}$

### APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low  $I_{RM}$
- Small 8.45 mm<sup>2</sup> foot print  
(See mounting pad details next page)

### MECHANICAL & PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S40•
- WEIGHT: 0.016 grams (approx.)
- Package dimension on last page
- Tape & Reel option: 12 mm tape per Standard EIA-481-B, 3000 on 7 inch reel and 12,000 on 13" reel

### THERMAL CHARACTERISTICS (UNLESS OTHERWISE SPECIFIED)

#### Thermal Resistance

Junction-to-case (bottom)	$R_{\theta JC}$	15	$^\circ\text{C}/\text{Watt}$
Junction-to-ambient (1)	$R_{\theta JA}$	240	$^\circ\text{C}/\text{Watt}$

(1) When mounted on FR-4 PC board using 1 oz copper with recommended minimum foot print

### DO-216

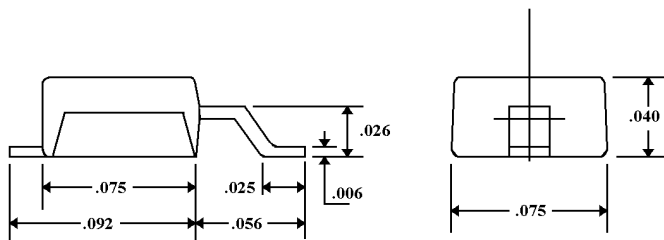
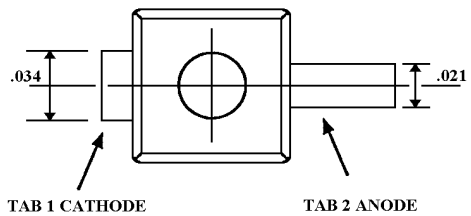


See further details and dimensions on last page

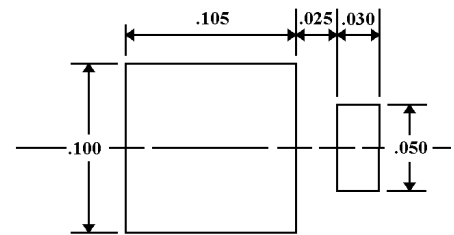
**ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)**

Parameter	Symbol	Conditions	Min	Typ.	Max	Units
Forward Voltage (Note 1)	$V_F$	$I_F = 0.1 \text{ A}$ $I_F = 1.0 \text{ A}$ $I_F = 3.0 \text{ A}$			0.36 0.45 0.75	V
Reverse Breakdown Voltage (Note 1)	$V_{BR}$	$I_R = 0.4 \text{ mA}$	40			V
Reverse Current (Note 1)	$I_R$	$V_R = 40 \text{ V}, T_J = 25 \text{ }^\circ\text{C}$			0.4	mA
Capacitance	$C_T$	$V_R = 5 \text{ V}; f = 1 \text{ MHz}$		70		pF

Note: 1 Short duration test pulse used to minimize self – heating effect.

**PACKAGE & MOUNTING PAD DIMENSIONS**


DO-216 Package (All dimensions +/- .005 inches)



MOUNTING PAD in inches